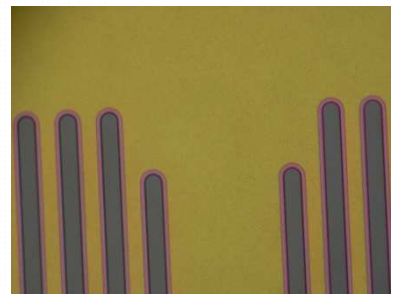


IBS propose a large range of technical process etching solution.

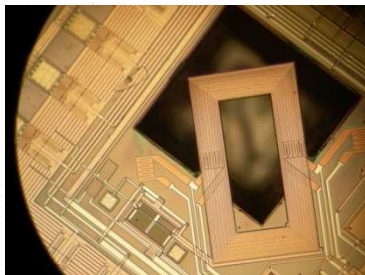
○ Dry & Wet etching

- Silicon oxide.
- Stripping: photoresist, polyimide.
- Metals: aluminium, titanium, gold, silver, Platinum, chromium, copper, nickel...
- Descum: to remove organics particules
- Nitride

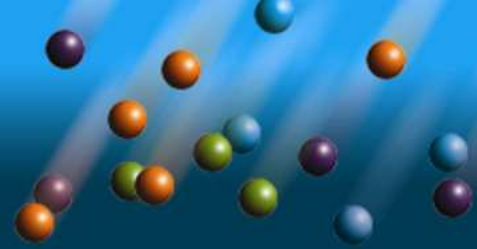


○ Ion beam etching

○ specific recipe etching with TMAH



- Silicon etching by TMAH:
 - Recipes for MEMS Technologies. (suspended structures)
 - Recipe compatible with MOS technologies.
 - Deep etching



Wet etching

- **Silicon oxide « SiO₂ »:** *photoresist withstand etching solution: 40 min*
 - etch rate **SiO₂** 600Å /min
 - selectivity **SiO₂/Si** ~10
 - selectivity **SiO₂/Al** ~10
 - selectivity **SiO₂/Ti** ~10
- **Silicon by TMAH :** *non compatible with photoresist // compatible CMOS*
 - etch rate **Si** 1,67µm/min (plan Si [100] orth)
 - etch rate **SiO₂** 3Å/min
- **Metals:** *compatible with photoresist*
 - etch rate **Al** 3400Å /min
 - etch rate **AlSi** 2800Å /min
 - etch rate **AlSiCu** 4500Å /min
 - etch rate **Cr** 2700Å /min
 - etch rate **Ti** 1110Å /min
 - etch rate **Mo** 12µm/min à 25°C; 25µm/min à t

For other request, please contact us

Dry etching

- *compatible with photoresist*
 - etch rate **SiO₂** 291Å /min
 - etch rate **Si₃N₄ nitride** 140Å /min
 - recipe deep etching: etch rate **Si** 1µm/min; etch rate **photoresist** 333Å /min
 - etch rate **SiC silicon carbide** 550Å /min

For other request, please contact us

The range of substrat size is : 2 inches to 8 inches.

